

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	180deg to PFL +/- 5.0deg	Wafer Vendor
	5.0	Overall Thickness	300.00 +/- 5.00 $\mu$ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00 $\mu$ m	Guaranteed by Process
	7.0	Bow	<60.00 $\mu$ m	ADE to ASTM F534, 20%
	8.0	Warp	<60.00 $\mu$ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Global Flatness (TIR)	<2.00 $\mu$ m	ADE, 100%
	12.0	Front Surface Quality	Polished. Max count 2 scratches, Max Total Scratch length 20mm. Orange peel, edge chips or other surface defects = None. Tweezer marks within edge exclusion zone at wafer edge acceptable.	Bright Light, 100% (note 2). No Sub-Surface Damage, Guaranteed by process.
	13.0	Backsurface condition	Polished. Max count 2 scratches, Max Scratch total length 20mm. Light handling marks. Tweezer marks within edge exclusion zone at wafer edge acceptable.	Bright Light, 100% (note2). No Sub-Surface Damage, Guaranteed by process.
HandleSilicon	14.0	Handle Silicon Raw Material	Prime Silicon	
	15.0	Handle Growth Method	MCZ	Wafer Vendor
	16.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	17.0	Handle Thickness	300.00 +/- 5.00 $\mu$ m	ADE, 100%
	18.0	Handle Doping Type	N	Wafer Vendor
	19.0	Handle Dopant	Phosphorous	Wafer Vendor
	20.0	Handle Resistivity	5 ~ 10 Ohmcm	Wafer Vendor
	21.0	Handle Oxygen Concentration	6.0ppma <= Oi <= 12.0ppma	Wafer vendor
HandleSilicon TopSurface	22.0	Laser scribe	Front Side, max length 7mm on one half of the flat length, not extending beyond the centre point. Dot Matrix, Small Font size 0.8mm X 0.4mm. Standard IceMOS Format: YYMM-XXXXX. Polishing after laser marking to remove burr.	Guaranteed by process
OverallWafer	23.0	Lasermarking	Laser scribe depth > / = 900nm	Guaranteed by process
HandleSilicon	24.0	Backside Lasermark	NO BACKSIDE LASERMARKING.	Guaranteed by process
	25.0	Surface Haze	None: Frontside and Backside.	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information